

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention

NON-DESTRUCTIVE EVALUATION OF MICROSTRUCTURE
AND INTERFACE ROUGHNESS OF ELECTRICALLY
CONDUCTING LINES IN SEMICONDUCTOR INTEGRATED
CIRCUITS IN DEEP SUB-MICRON REGIME

Application Number :

Confirmation Number:

First Named Applicant: Fen Chen

Attorney Docket Number: BUR920040182US1

Art Unit:

Examiner:

Search string: (6603321 or 20010046276).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	6603321	2003-08-05	Filippi, Jr. et al			

US Published Applications

Note: Applicant is not required to submit a paper copy of cited US Published Applications

init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
	1	20010046276	2001-11-29	Schneider et al			

Signature

Examiner Name	Date